



MG075R040

主要参数 MAIN CHARACTERISTICS

I_D	60A
V_{CE}	750V
$R_{dson-typ}$ (@ $V_{gs}=20V$)	25m Ω
Q_g-typ	130nC

用途

- 光伏逆变器
- 开关模式电源
- 高压 DC/DC 转换器
- 电池充电器
- 电动驱动
- 脉冲电源应用

APPLICATIONS

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications

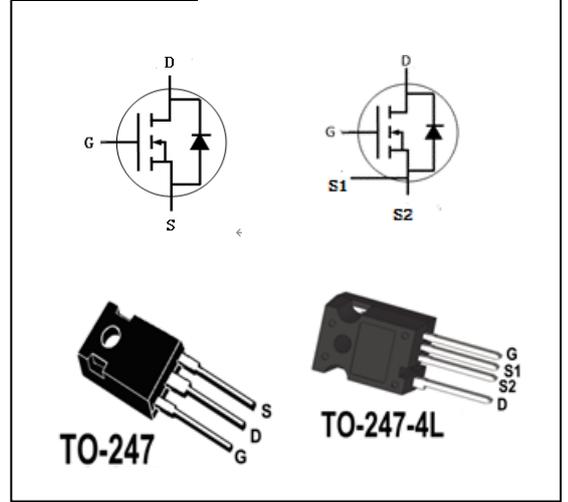
产品特性

- 高阻断电压
- 低导通电阻
- 低电容高速开关
- 易于驱动
- 雪崩强度高
- RoHS 产品

FEATURES

- High Blocking Voltage
- Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package
无卤-条管 Halogen-Free-Tube		
MG075R040-GH-BR	MG075R040	TO-247-4L
MG075R040-GE-BR	MG075R040	TO-247

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit	测试条件 Tests conditions
最高漏极-源极直流电压 Drain-Source Voltage	V_{DSmax}	750	V	$V_{GS}=0V, I_D=100\mu A$
最高栅源电压 Gate-Source Voltage	V_{GSmax}	-8/+22	V	Absolute maximum values
工作栅源电压 Gate-Source Voltage	V_{GSop}	-5/+18	V	Recommended operational values
连续漏极电流 Drain Current -continuous	I_D	60	A	$V_{GS}=20V, T_c=25^{\circ}\text{C}$
		40	A	$V_{GS}=20V, T_c=100^{\circ}\text{C}$
最大脉冲漏极电流 Drain Current - pulse	I_{DM}	130	A	Pulse width limited by T_{jmax}
耗散功率 Power Dissipation	P_D	400	W	$T_c=25^{\circ}\text{C}, T_j=175^{\circ}\text{C}$
最高结温及存储温度 Operating and Storage Temperature Range	T_J, T_{STG}	-55~+175	$^{\circ}\text{C}$	
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300	$^{\circ}\text{C}$	



电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
漏-源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=100\mu A, V_{GS}=0V$	900	-	-	V
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=5mA, T_C=25^\circ C$	2.0	3.2	4	V
		$V_{DS} = V_{GS}, I_D=5mA, T_C=175^\circ C$		2		
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=750V, V_{GS}=0V, T_C=25^\circ C$	-	2	100	μA
栅极体漏电流 Gate-body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS} =18V$	-	50	200	nA
导通电阻 Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} =18V, I_D=20A, T_C=25^\circ C$	-	25	40	m Ω
		$V_{GS} =18V, I_D=20A, T_C=175^\circ C$		35		m Ω
跨导 Transconductance	g_{fs}	$V_{DS} = 20V, I_D=20A, T_J = 25^\circ C$	-	9.4	-	S
		$V_{DS} = 20V, I_D=20A, T_J =175^\circ C$		11.9		S
输入电容 Input capacitance	C_{iss}	$V_{DS}=400V,$ $V_{GS} =0V,$ $f=1.0MHz,$ $V_{AC}=25 mV$	-	2600	-	pF
输出电容 Output capacitance	C_{oss}		-	300	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	30	-	pF
导通开关能量 Turn-On Switching Energy	E_{ON}	$V_{DS}=400V, V_{GS}=-5/20V, I_D= 10A,$ $R_{G(ext)} = 5\Omega, L= 142\mu H$	-	1.6	-	μJ
关断开关能量 Turn-Off Switching Energy	E_{OFF}		-	0.8	-	
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=400V, V_{GS}=-5/18V$ $I_D = 20A, \text{Timing relative to } V_{DS}$	-	15	-	ns
上升时间 Turn-On rise time	t_r		-	45	-	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	13	-	ns
下降时间 Turn-Off Fall time	t_f		-	10	-	ns
栅电阻 Intrinsic gate resistance	R_G	$f = 1 MHz, V_{AC}=25mV$	-	1.5	-	Ω
栅-源电荷 Gate-Source charge	Q_{gs}	$V_{DD}=400V, V_{GS}=-5/18V, I_D = 20A$		40		nC
栅-漏电荷 Gate-Drain charge	Q_{gd}			28		
栅极电荷总量 Total Gate Charge	Q_g			130		





漏-源二极管特性 Drain-Source Diode Characteristics

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	典型 Typ	最大 Max	单位 Units
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = -5V, I_{SD} = 10 A, T_J = 25\text{ }^\circ\text{C}$	5.5		V
		$V_{GS} = -5V, I_{SD} = 10 A, T_J = 175\text{ }^\circ\text{C}$	5.2		V
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	60	A
反向恢复时间 Reverse recovery time	t_{rr}		30		ns
反向恢复电荷 Reverse recovery charge	Q_{rr}	$V_{GS} = -5V, I_{SD} = 20 A, V_R = 400V,$ $di/dt = 1200A/\mu s$	120		nC
峰值反向恢复电流 Peak Reverse Recovery Current	I_{rrm}		10		A

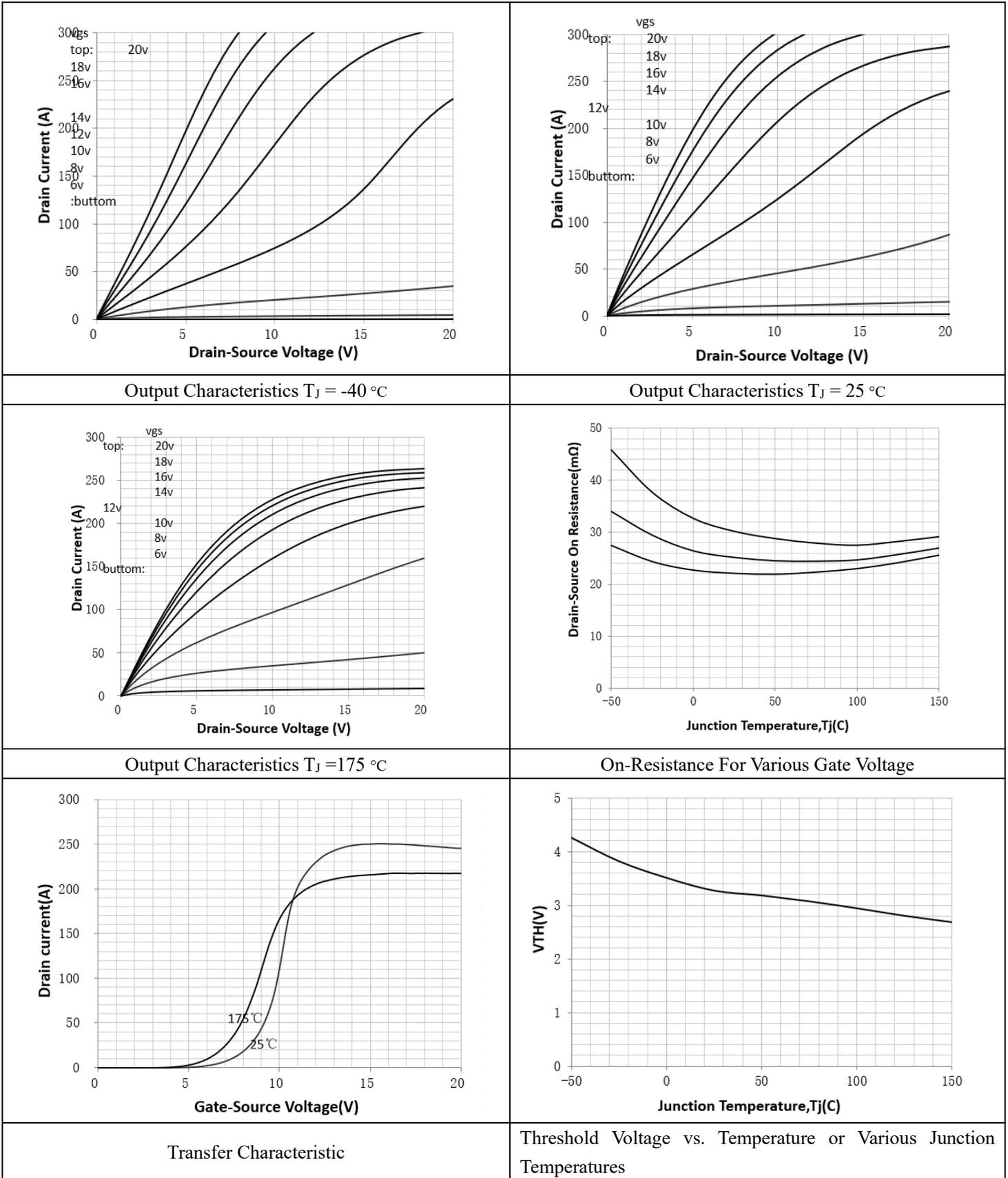
热特性 THERMAL CHARACTERISTIC

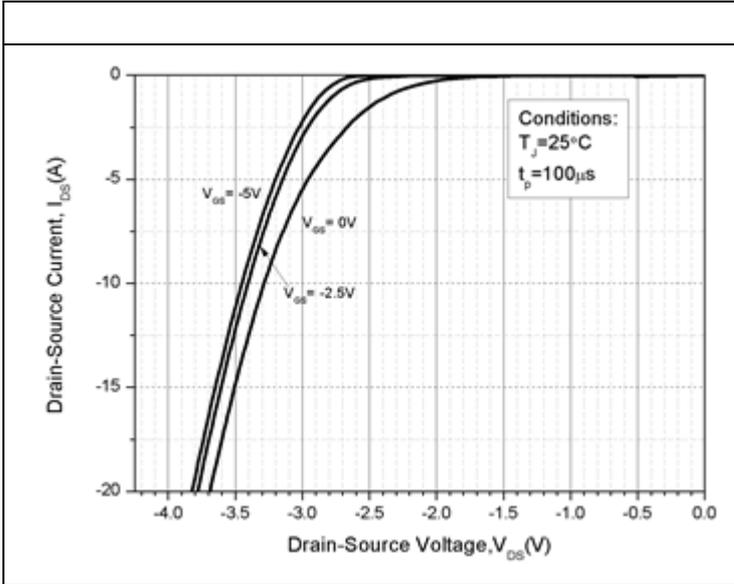
项 目 Parameter	符 号 Symbol	典型 Typ	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.32	$^\circ\text{C/W}$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	35	$^\circ\text{C/W}$



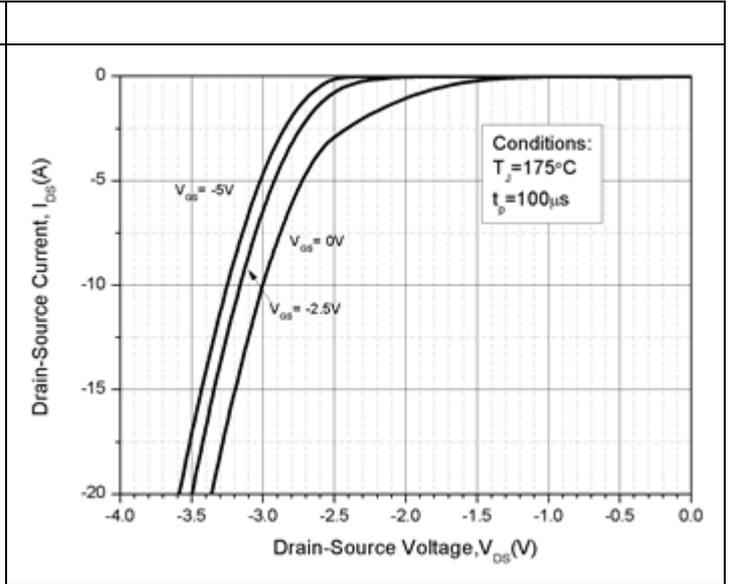


典型性能 Typical Performance

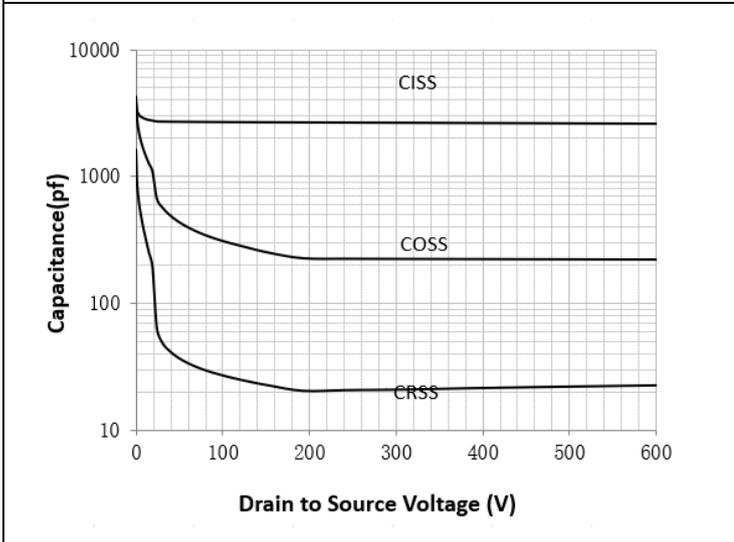




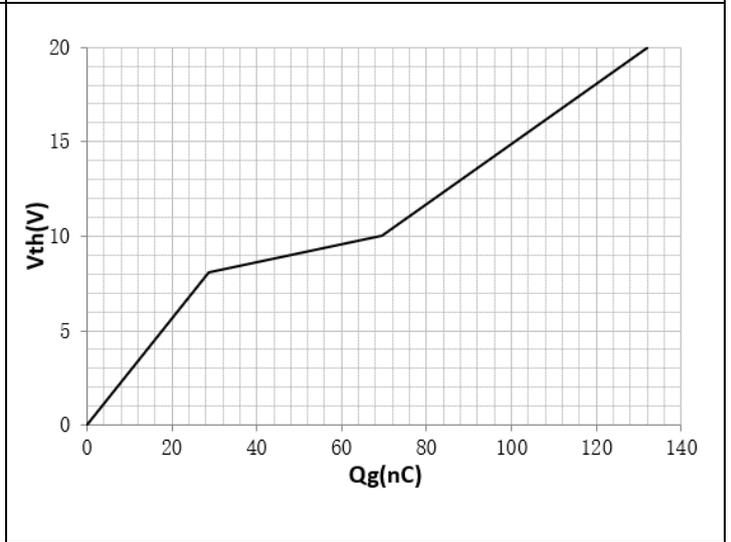
Body Diode Characteristics, $T_J = 25\text{ }^\circ\text{C}$



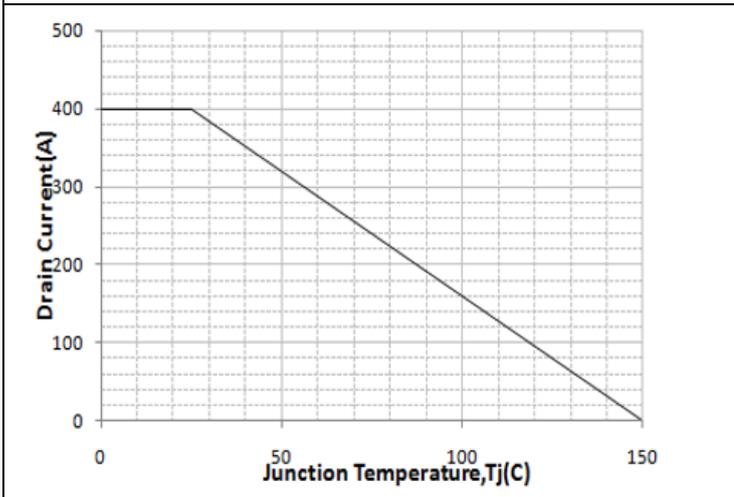
Body Diode Characteristics, $T_J = 175\text{ }^\circ\text{C}$



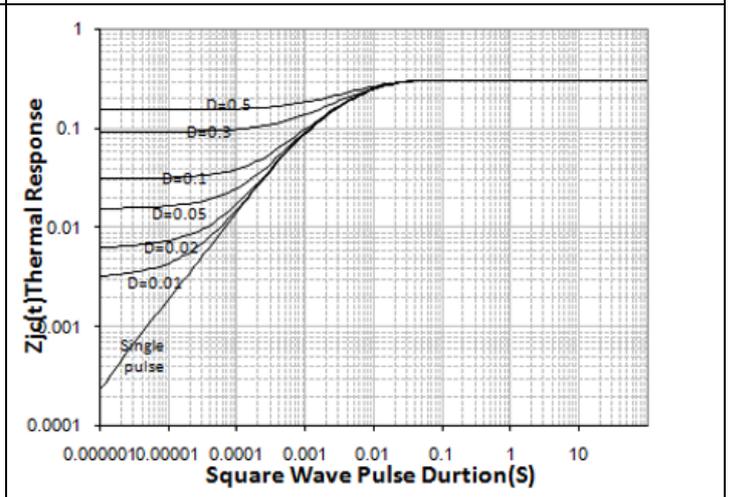
Capacitances vs. Drain-Source Voltage



Gate Charge Characteristics



Power Dissipation Derating

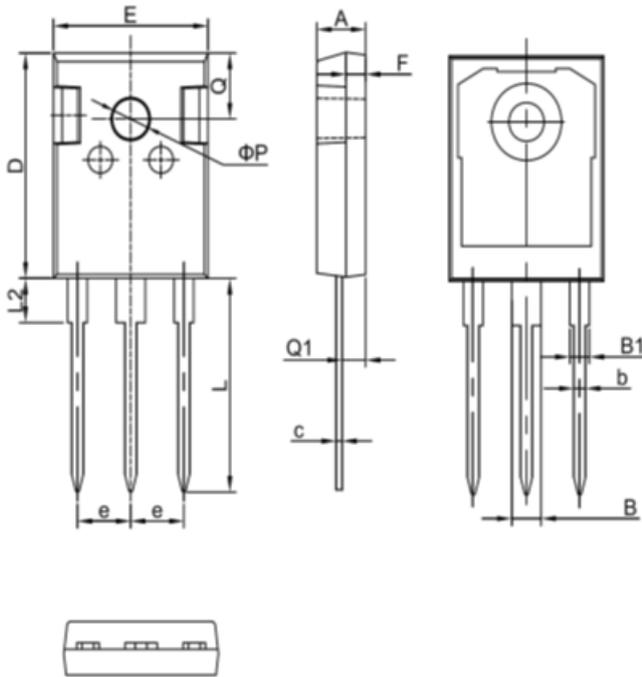


Transient Thermal Impedance



TO-247

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70

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联系方式

吉林华微电子股份有限公司

公司地址：吉林省吉林市深圳街 99 号

邮编：132013

总机：86-432-64678411

传真：86-432-64665812

网址：www.hwdz.com.cn

CONTACT

JILIN SINO-MICROELECTRONICS CO., LTD.

ADD: No.99 Shenzhen Street, Jilin City, Jilin Province, China.

Post Code: 132013

Tel: 86-432-64678411

Fax: 86-432-64665812

Web Site: www.hwdz.com.cn

